1. Cyclone III Device Datasheet

CIII52001-3.5

This chapter describes the electric characteristics, switching characteristics, and I/O timing for Cyclone® III devices. A glossary is also included for your reference.

Electrical Characteristics

The following sections provide information about the absolute maximum ratings, recommended operating conditions, DC characteristics, and other specifications for Cyclone III devices.

Operating Conditions

When Cyclone III devices are implemented in a system, they are rated according to a set of defined parameters. To maintain the highest possible performance and reliability of Cyclone III devices, system designers must consider the operating requirements in this document. Cyclone III devices are offered in commercial, industrial, and automotive grades. Commercial devices are offered in –6 (fastest), –7, and –8 speed grades. Industrial and automotive devices are offered only in –7 speed grade.

In this chapter, a prefix associated with the operating temperature range is attached to the speed grades; commercial with "C" prefix, industrial with "I" prefix, and automotive with "A" prefix. Commercial devices are therefore indicated as C6, C7, and C8 per respective speed grades. Industrial and automotive devices are indicated as I7 and A7, respectively.

Absolute Maximum Ratings

Absolute maximum ratings define the maximum operating conditions for Cyclone III devices. The values are based on experiments conducted with the device and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied at these conditions. Table 1–1 lists the absolute maximum ratings for Cyclone III devices.

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Conditions beyond those listed in Table 1–1 cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time has adverse effects on the device.

Table 1–1. Cyclone III Devices Absolute Maximum Ratings *(1)*

Symbol	Parameter	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic	–0.5	1.8	V
V_{CCIO}	Supply voltage for output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage (analog) for phase-locked loop (PLL) regulator	–0.5	3.75	V
V_{CCD_PLL}	Supply voltage (digital) for PLL	–0.5	1.8	V
V_I	DC input voltage	–0.5	3.95	V
I_{OUT}	DC output current, per pin	–25	40	mA
V_{ESDHBM}	Electrostatic discharge voltage using the human body model	—	±2000	V
V_{ESDCDM}	Electrostatic discharge voltage using the charged device model	—	±500	V
T_{STG}	Storage temperature	–65	150	°C
T_J	Operating junction temperature	–40	125	°C

Note to Table 1–1:

(1) Supply voltage specifications apply to voltage readings taken at the device pins with respect to ground, not at the power supply.

Maximum Allowed Overshoot or Undershoot Voltage

During transitions, input signals may overshoot to the voltage listed in Table 1–2 and undershoot to –2.0 V for a magnitude of currents less than 100 mA and for periods shorter than 20 ns. Table 1–2 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage over the lifetime of the device. The maximum allowed overshoot duration is specified as percentage of high-time over the lifetime of the device.

A DC signal is equivalent to 100% duty cycle. For example, a signal that overshoots to 4.2 V can only be at 4.2 V for 10.74% over the lifetime of the device; for device lifetime of 10 years, this amounts to 10.74/10ths of a year.

Table 1–2. Cyclone III Devices Maximum Allowed Overshoot During Transitions over a 10-Year Time Frame *(1)*

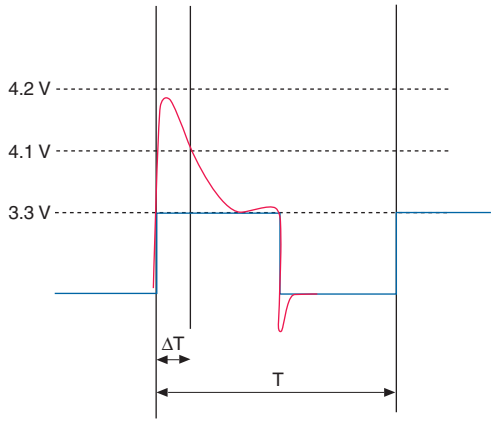
Symbol	Parameter	Condition	Overshoot Duration as % of High Time	Unit
V_i	AC Input Voltage	V_I = 3.95 V	100	%
		V_I = 4.0 V	95.67	%
		V_I = 4.05 V	55.24	%
		V_I = 4.10 V	31.97	%
		V_I = 4.15 V	18.52	%
		V_I = 4.20 V	10.74	%
		V_I = 4.25 V	6.23	%
		V_I = 4.30 V	3.62	%
		V_I = 4.35 V	2.1	%
		V_I = 4.40 V	1.22	%
		V_I = 4.45 V	0.71	%
		V_I = 4.50 V	0.41	%
		V_I = 4.60 V	0.14	%
		V_I = 4.70 V	0.047	%

Note to Table 1–2:

(1) Figure 1–1 shows the methodology to determine the overshoot duration. In the example in Figure 1–1, overshoot voltage is shown in red and is present on the input pin of the Cyclone III device at over 4.1 V but below 4.2 V. From Table 1–1, for an overshoot of 4.1 V, the percentage of high time for the overshoot can be as high as 31.97% over a 10-year period. Percentage of high time is calculated as ([delta T]/T) × 100. This 10-year period assumes the device is always turned on with 100% I/O toggle rate and 50% duty cycle signal. For lower I/O toggle rates and situations in which the device is in an idle state, lifetimes are increased.

Figure 1–1 shows the methodology to determine the overshoot duration.

Figure 1–1. Cyclone III Devices Overshoot Duration



Recommended Operating Conditions

This section lists the functional operation limits for AC and DC parameters for Cyclone III devices. The steady-state voltage and current values expected from Cyclone III devices are provided in Table 1–3. All supplies must be strictly monotonic without plateaus.

Table 1–3. Cyclone III Devices Recommended Operating Conditions *(1), (2)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CCINT} *(3)*	Supply voltage for internal logic	—	1.15	1.2	1.25	V
V_{CCIO} *(3), (4)*	Supply voltage for output buffers, 3.3-V operation	—	3.135	3.3	3.465	V
	Supply voltage for output buffers, 3.0-V operation	—	2.85	3	3.15	V
	Supply voltage for output buffers, 2.5-V operation	—	2.375	2.5	2.625	V
	Supply voltage for output buffers, 1.8-V operation	—	1.71	1.8	1.89	V
	Supply voltage for output buffers, 1.5-V operation	—	1.425	1.5	1.575	V
	Supply voltage for output buffers, 1.2-V operation	—	1.14	1.2	1.26	V
V_{CCA} *(3)*	Supply (analog) voltage for PLL regulator	—	2.375	2.5	2.625	V
V_{CCD_PLL} *(3)*	Supply (digital) voltage for PLL	—	1.15	1.2	1.25	V
V_I	Input voltage	—	–0.5	—	3.6	V
V_O	Output voltage	—	0	—	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	—	85	°C
		For industrial use	–40	—	100	°C
		For extended temperature	–40	—	125	°C
		For automotive use	–40	—	125	°C
t_{RAMP}	Power supply ramp time	Standard power-on reset (POR) *(5)*	50 µs	—	50 ms	—
		Fast POR *(6)*	50 µs	—	3 ms	—
I_{Diode}	Magnitude of DC current across PCI-clamp diode when enabled	—	—	—	10	mA

Notes to Table 1–3:

(1) V_{CCIO} for all I/O banks must be powered up during device operation. All V_{CCA} pins must be powered to 2.5 V (even when PLLs are not used), and must be powered up and powered down at the same time.

(2) V_{CCD_PLL} must always be connected to V_{CCINT} through a decoupling capacitor and ferrite bead.

(3) The V_{CC} must rise monotonically.

(4) All input buffers are powered by the V_{CCIO} supply.

(5) POR time for Standard POR ranges between 50–200 ms. Each individual power supply should reach the recommended operating range within 50 ms.

(6) POR time for Fast POR ranges between 3–9 ms. Each individual power supply should reach the recommended operating range within 3 ms.

DC Characteristics

This section lists the I/O leakage current, pin capacitance, on-chip termination (OCT) tolerance, and bus hold specifications for Cyclone III devices.

Supply Current

Standby current is the current the device draws after the device is configured with no inputs or outputs toggling and no activity in the device. Use the Excel-based early power estimator (EPE) to get the supply current estimates for your design because these currents vary largely with the resources used. Table 1–4 lists I/O pin leakage current for Cyclone III devices.

For more information about power estimation tools, refer to the *PowerPlay Early Power Estimator User Guide* and the *PowerPlay Power Analysis* chapter in the *Quartus II Handbook*.

Table 1–4. Cyclone III Devices I/O Pin Leakage Current *(1), (2)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	Input pin leakage current	V_I = 0 V to $V_{CCIOMAX}$	–10	—	10	µA
I_{OZ}	Tristated I/O pin leakage current	V_O = 0 V to $V_{CCIOMAX}$	–10	—	10	µA

Notes to Table 1–4:

(1) This value is specified for normal device operation. The value varies during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, and 1.2 V).

(2) 10 µA I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be the observed when the diode is on.

Bus Hold

Bus hold retains the last valid logic state after the source driving it either enters the high impedance state or is removed. Each I/O pin has an option to enable bus hold in user mode. Bus hold is always disabled in configuration mode.

Table 1–5 lists bus hold specifications for Cyclone III devices.

Table 1–5. Cyclone III Devices Bus Hold Parameter ***(Part 1 of 2)*** *(1)*

Parameter	Condition	V_{CCIO} (V)												Unit
		1.2		1.5		1.8		2.5		3.0		3.3		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus-hold low, sustaining current	$V_{IN} > V_{IL}$ (maximum)	8	—	12	—	30	—	50	—	70	—	70	—	µA
Bus-hold high, sustaining current	$V_{IN} < V_{IL}$ (minimum)	–8	—	–12	—	–30	—	–50	—	–70	—	–70	—	µA

Table 1–5. Cyclone III Devices Bus Hold Parameter *(Part 2 of 2)* (1)

Parameter	Condition	V_{CCIO} (V)												Unit
		1.2		1.5		1.8		2.5		3.0		3.3		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus-hold low, overdrive current	0 V < V_{IN} < V_{CCIO}	—	125	—	175	—	200	—	300	—	500	—	500	µA
Bus-hold high, overdrive current	0 V < V_{IN} < V_{CCIO}	—	–125	—	–175	—	–200	—	–300	—	–500	—	–500	µA
Bus-hold trip point	—	0.3	0.9	0.375	1.125	0.68	1.07	0.7	1.7	0.8	2	0.8	2	V

Note to Table 1–5:

(1) The bus-hold trip points are based on calculated input voltages from the JEDEC standard.

OCT Specifications

Table 1–6 lists the variation of OCT without calibration across process, temperature, and voltage.

Table 1–6. Cyclone III Devices Series OCT without Calibration Specifications

Description	V_{CCIO} (V)	Resistance Tolerance		Unit
		Commercial Max	Industrial and Automotive Max	
Series OCT without calibration	3.0	±30	±40	%
	2.5	±30	±40	%
	1.8	+40	±50	%
	1.5	+50	±50	%
	1.2	+50	±50	%

OCT calibration is automatically performed at device power-up for OCT enabled I/Os.

Table 1–7 lists the OCT calibration accuracy at device power-up.

Table 1–7. Cyclone III Devices Series OCT with Calibration at Device Power-Up Specifications

Description	V_{CCIO} (V)	Calibration Accuracy		Unit
		Commercial Max	Industrial and Automotive Max	
Series OCT with calibration at device power-up	3.0	±10	±10	%
	2.5	±10	±10	%
	1.8	±10	±10	%
	1.5	±10	±10	%
	1.2	±10	±10	%

The OCT resistance may vary with the variation of temperature and voltage after calibration at device power-up. Use Table 1–8 and Equation 1–1 to determine the final OCT resistance considering the variations after calibration at device power-up. Table 1–8 lists the change percentage of the OCT resistance with voltage and temperature.

Table 1–8. Cyclone III Devices OCT Variation After Calibration at Device Power-Up

Nominal Voltage	dR/dT (%/°C)	dR/dV (%/mV)
3.0	0.262	–0.026
2.5	0.234	–0.039
1.8	0.219	–0.086
1.5	0.199	–0.136
1.2	0.161	–0.288

Equation 1–1. *(1), (2), (3), (4), (5), (6)*

$$\Delta R_V = (V_2 - V_1) \times 1000 \times dR/dV \quad (7)$$

$$\Delta R_T = (T_2 - T_1) \times dR/dT \quad (8)$$

$$\text{For } \Delta R_x < 0;\ MF_x = 1/(|\Delta R_x|/100 + 1) \quad (9)$$

$$\text{For } \Delta R_x > 0;\ MF_x = \Delta R_x/100 + 1 \quad (10)$$

$$MF = MF_V \times MF_T \quad (11)$$

$$R_{final} = R_{initial} \times MF \quad (12)$$

Notes to Equation 1–1:

(1) T_2 is the final temperature.
(2) T_1 is the initial temperature.
(3) MF is multiplication factor.
(4) R_{final} is final resistance.
(5) $R_{initial}$ is initial resistance.
(6) Subscript × refers to both $_V$ and $_T$.
(7) ΔR_V is variation of resistance with voltage.
(8) ΔR_T is variation of resistance with temperature.
(9) dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
(10) dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
(11) V_2 is final voltage.
(12) V_1 is the initial voltage.

Example 1–1 shows you the example to calculate the change of 50 Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V:

Example 1–1.

$\Delta R_V = (3.15 - 3) \times 1000 \times -0.026 = -3.83$

$\Delta R_T = (85 - 25) \times 0.262 = 15.72$

Because ΔR_V is negative,

$MF_V = 1 / (3.83/100 + 1) = 0.963$

Because ΔR_T is positive,

$MF_T = 15.72/100 + 1 = 1.157$

$MF = 0.963 \times 1.157 = 1.114$

$R_{final} = 50 \times 1.114 = 55.71\ \Omega$

Pin Capacitance

Table 1–9 lists the pin capacitance for Cyclone III devices.

Table 1–9. Cyclone III Devices Pin Capacitance

Symbol	Parameter	Typical – QFP	Typical – FBGA	Unit
C_{IOTB}	Input capacitance on top/bottom I/O pins	7	6	pF
C_{IOLR}	Input capacitance on left/right I/O pins	7	5	pF
C_{LVDSLR}	Input capacitance on left/right I/O pins with dedicated LVDS output	8	7	pF
C_{VREFLR} (1)	Input capacitance on left/right dual-purpose VREF pin when used as V_{REF} or user I/O pin	21	21	pF
C_{VREFTB} (1)	Input capacitance on top/bottom dual-purpose VREF pin when used as V_{REF} or user I/O pin	23 (2)	23 (2)	pF
C_{CLKTB}	Input capacitance on top/bottom dedicated clock input pins	7	6	pF
C_{CLKLR}	Input capacitance on left/right dedicated clock input pins	6	5	pF

Notes to Table 1–9:

(1) When VREF pin is used as regular input or output, a reduced performance of toggle rate and t_{CO} is expected due to higher pin capacitance.

(2) C_{VREFTB} for EP3C25 is 30 pF.

Internal Weak Pull-Up and Weak Pull-Down Resistor

Table 1–10 lists the weak pull-up and pull-down resistor values for Cyclone III devices.

Table 1–10. Cyclone III Devices Internal Weak Pull-Up and Weak Pull-Down Resistor *(1)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{_PU}$	Value of I/O pin pull-up resistor before and during configuration, as well as user mode if the programmable pull-up resistor option is enabled	V_{CCIO} = 3.3 V ± 5% *(2), (3)*	7	25	41	kΩ
		V_{CCIO} = 3.0 V ± 5% *(2), (3)*	7	28	47	kΩ
		V_{CCIO} = 2.5 V ± 5% *(2), (3)*	8	35	61	kΩ
		V_{CCIO} = 1.8 V ± 5% *(2), (3)*	10	57	108	kΩ
		V_{CCIO} = 1.5 V ± 5% *(2), (3)*	13	82	163	kΩ
		V_{CCIO} = 1.2 V ± 5% *(2), (3)*	19	143	351	kΩ
$R_{_PD}$	Value of I/O pin pull-down resistor before and during configuration	V_{CCIO} = 3.3 V ± 5% *(4)*	6	19	30	kΩ
		V_{CCIO} = 3.0 V ± 5% *(4)*	6	22	36	kΩ
		V_{CCIO} = 2.5 V ± 5% *(4)*	6	25	43	kΩ
		V_{CCIO} = 1.8 V ± 5% *(4)*	7	35	71	kΩ
		V_{CCIO} = 1.5 V ± 5% *(4)*	8	50	112	kΩ

Notes to Table 1–10:

(1) All I/O pins have an option to enable weak pull-up except configuration, test, and JTAG pin. Weak pull-down feature is only available for JTAG TCK.

(2) Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.

(3) $R_{_PU} = (V_{CCIO} – V_I)/I_{R_PU}$
Minimum condition: –40°C; $V_{CCIO} = V_{CC}$ + 5%, $V_I = V_{CC}$ + 5% – 50 mV;
Typical condition: 25°C; $V_{CCIO} = V_{CC}$, V_I = 0 V;
Maximum condition: 125°C; $V_{CCIO} = V_{CC}$ – 5%, V_I = 0 V; in which V_I refers to the input voltage at the I/O pin.

(4) $R_{_PD} = V_I/I_{R_PD}$
Minimum condition: –40°C; $V_{CCIO} = V_{CC}$ + 5%, V_I = 50 mV;
Typical condition: 25°C; $V_{CCIO} = V_{CC}$, $V_I = V_{CC}$ – 5%;
Maximum condition: 125°C; $V_{CCIO} = V_{CC}$ – 5%, $V_I = V_{CC}$ – 5%; in which V_I refers to the input voltage at the I/O pin.

Hot Socketing

Table 1–11 lists the hot-socketing specifications for Cyclone III devices.

Table 1–11. Cyclone III Devices Hot-Socketing Specifications

Symbol	Parameter	Maximum
$I_{IOPIN(DC)}$	DC current per I/O pin	300 µA
$I_{IOPIN(AC)}$	AC current per I/O pin	8 mA *(1)*

Note to Table 1–11:

(1) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, |IIOPIN| = C dv/dt, in which C is I/O pin capacitance and dv/dt is the slew rate.

Schmitt Trigger Input

Cyclone III devices support Schmitt trigger input on TDI, TMS, TCK, nSTATUS, nCONFIG, nCE, CONF_DONE, and DCLK pins. A Schmitt trigger feature introduces hysteresis to the input signal for improved noise immunity, especially for signal with slow edge rate. Table 1–12 lists the hysteresis specifications across supported V_{CCIO} range for Schmitt trigger inputs in Cyclone III devices.

Table 1–12. Hysteresis Specifications for Schmitt Trigger Input in Cyclone III Devices

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
$V_{SCHMITT}$	Hysteresis for Schmitt trigger input	V_{CCIO} = 3.3 V	200	—	—	mV
		V_{CCIO} = 2.5 V	200	—	—	mV
		V_{CCIO} = 1.8 V	140	—	—	mV
		V_{CCIO} = 1.5 V	110	—	—	mV

I/O Standard Specifications

The following tables list input voltage sensitivities (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by Cyclone III devices. Table 1–13 through Table 1–18 provide the I/O standard specifications for Cyclone III devices.

Table 1–13. Cyclone III Devices Single-Ended I/O Standard Specifications *(1), (2)*

I/O Standard	V_{CCIO} (V)			V_{IL} (V)		V_{IH} (V)		V_{OL} (V)	V_{OH} (V)	I_{OL} (mA)	I_{OH} (mA)
	Min	Typ	Max	Min	Max	Min	Max	Max	Min		
3.3-V LVTTL *(3)*	3.135	3.3	3.465	—	0.8	1.7	3.6	0.45	2.4	4	–4
3.3-V LVCMOS *(3)*	3.135	3.3	3.465	—	0.8	1.7	3.6	0.2	V_{CCIO} – 0.2	2	–2
3.0-V LVTTL *(3)*	2.85	3.0	3.15	–0.3	0.8	1.7	V_{CCIO} + 0.3	0.45	2.4	4	–4
3.0-V LVCMOS *(3)*	2.85	3.0	3.15	–0.3	0.8	1.7	V_{CCIO} + 0.3	0.2	V_{CCIO} – 0.2	0.1	–0.1
2.5-V LVTTL and LVCMOS *(3)*	2.375	2.5	2.625	–0.3	0.7	1.7	3.6	0.4	2.0	1	–1
1.8-V LVTTL and LVCMOS	1.71	1.8	1.89	–0.3	0.35 * V_{CCIO}	0.65 * V_{CCIO}	2.25	0.45	V_{CCIO} – 0.45	2	–2
1.5-V LVCMOS	1.425	1.5	1.575	–0.3	0.35 * V_{CCIO}	0.65 * V_{CCIO}	V_{CCIO} + 0.3	0.25 * V_{CCIO}	0.75 * V_{CCIO}	2	–2
1.2-V LVCMOS	1.14	1.2	1.26	–0.3	0.35 * V_{CCIO}	0.65 * V_{CCIO}	V_{CCIO} + 0.3	0.25 * V_{CCIO}	0.75 * V_{CCIO}	2	–2
3.0-V PCI	2.85	3.0	3.15	—	0.3 * V_{CCIO}	0.5 * V_{CCIO}	V_{CCIO} + 0.3	0.1 * V_{CCIO}	0.9 * V_{CCIO}	1.5	–0.5
3.0-V PCI-X	2.85	3.0	3.15	—	0.35* V_{CCIO}	0.5 * V_{CCIO}	V_{CCIO} + 0.3	0.1 * V_{CCIO}	0.9 * V_{CCIO}	1.5	–0.5

Notes to Table 1–13:

(1) For voltage referenced receiver input waveform and explanation of terms used in Table 1–13, refer to "Single-ended Voltage referenced I/O Standard" in "Glossary" on page 1–27.

(2) AC load CL = 10 pF.

(3) For more detail about interfacing Cyclone III devices with 3.3/3.0/2.5-V LVTTL/LVCMOS I/O standards, refer to *AN 447: Interfacing Cyclone III Devices with 3.3/3.0/2.5-V LVTTL and LVCMOS I/O Systems*.

Table 1–14. Cyclone III Devices Single-Ended SSTL and HSTL I/O Reference Voltage Specifications *(1)*

I/O Standard	V_{CCIO} (V)			V_{REF} (V)			V_{TT} (V) *(2)*		
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
SSTL-2 Class I, II	2.375	2.5	2.625	1.19	1.25	1.31	V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04
SSTL-18 Class I, II	1.7	1.8	1.9	0.833	0.9	0.969	V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	0.85	0.9	0.95
HSTL-15 Class I, II	1.425	1.5	1.575	0.71	0.75	0.79	0.71	0.75	0.79
HSTL-12 Class I, II	1.14	1.2	1.26	0.48 * V_{CCIO} *(3)* 0.47 * V_{CCIO} *(4)*	0.5 * V_{CCIO} *(3)* 0.5 * V_{CCIO} *(4)*	0.52 * V_{CCIO} *(3)* 0.53 * V_{CCIO} *(4)*	—	0.5 * V_{CCIO}	—

Notes to Table 1–14:

(1) For an explanation of terms used in Table 1–14, refer to "Glossary" on page 1–27.
(2) V_{TT} of transmitting device must track V_{REF} of the receiving device.
(3) Value shown refers to DC input reference voltage, $V_{REF(DC)}$.
(4) Value shown refers to AC input reference voltage, $V_{REF(AC)}$.

Table 1–15. Cyclone III Devices Single-Ended SSTL and HSTL I/O Standards Signal Specifications

I/O Standard	$V_{IL(DC)}$ (V)		$V_{IH(DC)}$ (V)		$V_{IL(AC)}$ (V)		$V_{IH(AC)}$ (V)		V_{OL} (V)	V_{OH} (V)	I_{OL} (mA)	I_{OH} (mA)
	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min		
SSTL-2 Class I	—	V_{REF} – 0.18	V_{REF} + 0.18	—	—	V_{REF} – 0.35	V_{REF} + 0.35	—	V_{TT} – 0.57	V_{TT} + 0.57	8.1	–8.1
SSTL-2 Class II	—	V_{REF} – 0.18	V_{REF} + 0.18	—	—	V_{REF} – 0.35	V_{REF} + 0.35	—	V_{TT} – 0.76	V_{TT} + 0.76	16.4	–16.4
SSTL-18 Class I	—	V_{REF} – 0.125	V_{REF} + 0.125	—	—	V_{REF} – 0.25	V_{REF} + 0.25	—	V_{TT} – 0.475	V_{TT} + 0.475	6.7	–6.7
SSTL-18 Class II	—	V_{REF} – 0.125	V_{REF} + 0.125	—	—	V_{REF} – 0.25	V_{REF} + 0.25	—	0.28	V_{CCIO} – 0.28	13.4	–13.4
HSTL-18 Class I	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	8	–8
HSTL-18 Class II	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	16	–16
HSTL-15 Class I	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	8	–8
HSTL-15 Class II	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	16	–16
HSTL-12 Class I	–0.15	V_{REF} – 0.08	V_{REF} + 0.08	V_{CCIO} + 0.15	–0.24	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCIO} + 0.24	0.25 × V_{CCIO}	0.75 × V_{CCIO}	8	–8
HSTL-12 Class II	–0.15	V_{REF} – 0.08	V_{REF} + 0.08	V_{CCIO} + 0.15	–0.24	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCIO} + 0.24	0.25 × V_{CCIO}	0.75 × V_{CCIO}	14	–14

For more illustrations of receiver input and transmitter output waveforms, and for other differential I/O standards, refer to the *High-Speed Differential Interfaces in Cyclone III Devices* chapter.

Table 1–16. Cyclone III Devices Differential SSTL I/O Standard Specifications *(1)*

I/O Standard	V_{CCIO} (V)			$V_{Swing(DC)}$ (V)		$V_{X(AC)}$ (V)			$V_{Swing(AC)}$ (V)		$V_{OX(AC)}$ (V)		
	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Max	Min	Typ	Max
SSTL-2 Class I, II	2.375	2.5	2.625	0.36	V_{CCIO}	$V_{CCIO}/2 - 0.2$	—	$V_{CCIO}/2 + 0.2$	0.7	V_{CCIO}	$V_{CCIO}/2 - 0.125$	—	$V_{CCIO}/2 + 0.125$
SSTL-18 Class I, II	1.7	1.8	1.90	0.25	V_{CCIO}	$V_{CCIO}/2 - 0.175$	—	$V_{CCIO}/2 + 0.175$	0.5	V_{CCIO}	$V_{CCIO}/2 - 0.125$	—	$V_{CCIO}/2 + 0.125$

Note to Table 1–16:

(1) Differential SSTL requires a V_{REF} input.

Table 1–17. Cyclone III Devices Differential HSTL I/O Standard Specifications *(1)*

I/O Standard	V_{CCIO} (V)			$V_{DIF(DC)}$ (V)		$V_{X(AC)}$ (V)			$V_{CM(DC)}$ (V)			$V_{DIF(AC)}$ (V)	
	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max	Min	Max
HSTL-18 Class I, II	1.71	1.8	1.89	0.2	—	0.85	—	0.95	0.85	—	0.95	0.4	—
HSTL-15 Class I, II	1.425	1.5	1.575	0.2	—	0.71	—	0.79	0.71	—	0.79	0.4	—
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V_{CCIO}	0.48 * V_{CCIO}	—	0.52 * V_{CCIO}	0.48 * V_{CCIO}	—	0.52 * V_{CCIO}	0.3	0.48 * V_{CCIO}

Note to Table 1–17:

(1) Differential HSTL requires a V_{REF} input.

Table 1–18. Cyclone III Devices Differential I/O Standard Specifications *(1)* **(Part 1 of 2)**

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) *(2)*			V_{OD} (mV) *(3)*			V_{OS} (V) *(3)*		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
LVPECL (Row I/Os) *(4)*	2.375	2.5	2.625	100	—	0.05	$D_{MAX} \leq$ 500 Mbps	1.80	—	—	—	—	—	—
						0.55	500 Mbps $\leq D_{MAX} \leq$ 700 Mbps	1.80						
						1.05	$D_{MAX} >$ 700 Mbps	1.55						
LVPECL (Column I/Os) *(4)*	2.375	2.5	2.625	100	—	0.05	$D_{MAX} \leq$ 500 Mbps	1.80	—	—	—	—	—	—
						0.55	500 Mbps $\leq D_{MAX} \leq$ 700 Mbps	1.80						
						1.05	$D_{MAX} >$ 700 Mbps	1.55						
LVDS (Row I/Os)	2.375	2.5	2.625	100	—	0.05	$D_{MAX} \leq$ 500 Mbps	1.80	247	—	600	1.125	1.25	1.375
						0.55	500 Mbps $\leq D_{MAX} \leq$ 700 Mbps	1.80						
						1.05	$D_{MAX} >$ 700 Mbps	1.55						

Table 1–18. Cyclone III Devices Differential I/O Standard Specifications (1) (Part 2 of 2)

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{IcM} (V) (2)			V_{OD} (mV) (3)			V_{OS} (V) (3)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
LVDS (Column I/Os)	2.375	2.5	2.625	100	—	0.05	$D_{MAX} \leq$ 500 Mbps	1.80	247	—	600	1.125	1.25	1.375
						0.55	500 Mbps $\leq D_{MAX} \leq$ 700 Mbps	1.80						
						1.05	D_{MAX} > 700 Mbps	1.55						
BLVDS (Row I/Os) (5)	2.375	2.5	2.625	100	—	—	—	—	—	—	—	—	—	—
BLVDS (Column I/Os) (5)	2.375	2.5	2.625	100	—	—	—	—	—	—	—	—	—	—
mini-LVDS (Row I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	300	—	600	1.0	1.2	1.4
mini-LVDS (Column I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	300	—	600	1.0	1.2	1.4
RSDS® (Row I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.5
RSDS (Column I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.5
PPDS® (Row I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.4
PPDS (Column I/Os) (6)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.4

Notes to Table 1–18:

(1) For an explanation of terms used in Table 1–18, refer to "Transmitter Output Waveform" in "Glossary" on page 1–27.
(2) V_{IN} range: 0 V $\leq V_{IN} \leq$ 1.85 V.
(3) R_L range: 90 $\leq R_L \leq$ 110 Ω.
(4) LVPECL input standard is only supported at clock input. Output standard is not supported.
(5) No fixed V_{IN}, V_{OD}, and V_{OS} specifications for BLVDS. They are dependent on the system topology.
(6) Mini-LVDS, RSDS, and PPDS standards are only supported at the output pins for Cyclone III devices.

Power Consumption

You can use the following methods to estimate power for a design:

- the Excel-based EPE.
- the Quartus II PowerPlay power analyzer feature.

The interactive Excel-based EPE is used prior to designing the device to get a magnitude estimate of the device power. The Quartus II PowerPlay power analyzer provides better quality estimates based on the specifics of the design after place-and-route is complete. The PowerPlay power analyzer can apply a combination of user-entered, simulation-derived, and estimated signal activities which, combined with detailed circuit models, can yield very accurate power estimates.

For more information about power estimation tools, refer to the *Early Power Estimator User Guide* and the *PowerPlay Power Analysis* chapter in volume 3 of the *Quartus II Handbook*.

Switching Characteristics

This section provides the performance characteristics of the core and periphery blocks for Cyclone III devices. All data is final and is based on actual silicon characterization and testing. These numbers reflect the actual performance of the device under worst-case silicon process, voltage, and junction temperature conditions.

Core Performance Specifications

Clock Tree Specifications

Table 1–19 lists the clock tree specifications for Cyclone III devices.

Table 1–19. Cyclone III Devices Clock Tree Performance

Device	Performance			Unit
	C6	C7	C8	
EP3C5	500	437.5	402	MHz
EP3C10	500	437.5	402	MHz
EP3C16	500	437.5	402	MHz
EP3C25	500	437.5	402	MHz
EP3C40	500	437.5	402	MHz
EP3C55	500	437.5	402	MHz
EP3C80	500	437.5	402	MHz
EP3C120	(1)	437.5	402	MHz

Note to Table 1–19:

(1) EP3C120 offered in C7, C8, and I7 grades only.

PLL Specifications

Table 1–20 describes the PLL specifications for Cyclone III devices when operating in the commercial junction temperature range (0°C to 85°C), the industrial junction temperature range (–40°C to 100°C), and the automotive junction temperature range (–40°Cto 125°C). For more information about PLL block, refer to "PLL Block" in "Glossary" on page 1–27.

Table 1–20. Cyclone III Devices PLL Specifications (1) (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
f_{IN} (2)	Input clock frequency	5	—	472.5	MHz
f_{INPFD}	PFD input frequency	5	—	325	MHz
f_{VCO} (3)	PLL internal VCO operating range	600	—	1300	MHz
f_{INDUTY}	Input clock duty cycle	40	—	60	%
$t_{INJITTER_CCJ}$ (4)	Input clock cycle-to-cycle jitter for $F_{INPFD} \geq 100$ MHz	—	—	0.15	UI
	Input clock cycle-to-cycle jitter for $F_{INPFD} < 100$ MHz	—	—	±750	ps
f_{OUT_EXT} (external clock output) (2)	PLL output frequency	—	—	472.5	MHz
f_{OUT} (to global clock)	PLL output frequency (–6 speed grade)	—	—	472.5	MHz
	PLL output frequency (–7 speed grade)	—	—	450	MHz
	PLL output frequency (–8 speed grade)	—	—	402.5	MHz
$t_{OUTDUTY}$	Duty cycle for external clock output (when set to 50%)	45	50	55	%
t_{LOCK}	Time required to lock from end of device configuration	—	—	1	ms
t_{DLOCK}	Time required to lock dynamically (after switchover, reconfiguring any non-post-scale counters/delays or areset is deasserted)	—	—	1	ms
$t_{OUTJITTER_PERIOD_DEDCLK}$ (5)	Dedicated clock output period jitter $F_{OUT} \geq 100$ MHz	—	—	300	ps
	$F_{OUT} < 100$ MHz	—	—	30	mUI
$t_{OUTJITTER_CCJ_DEDCLK}$ (5)	Dedicated clock output cycle-to-cycle jitter $F_{OUT} \geq 100$ MHz	—	—	300	ps
	$F_{OUT} < 100$ MHz	—	—	30	mUI
$t_{OUTJITTER_PERIOD_IO}$ (5)	Regular I/O period jitter $F_{OUT} \geq 100$ MHz	—	—	650	ps
	$F_{OUT} < 100$ MHz	—	—	75	mUI
$t_{OUTJITTER_CCJ_IO}$ (5)	Regular I/O cycle-to-cycle jitter $F_{OUT} \geq 100$ MHz	—	—	650	ps
	$F_{OUT} < 100$ MHz	—	—	75	mUI
t_{PLL_PSERR}	Accuracy of PLL phase shift	—	—	±50	ps
t_{ARESET}	Minimum pulse width on areset signal.	10	—	—	ns
$t_{CONFIGPLL}$	Time required to reconfigure scan chains for PLLs	—	3.5 (6)	—	SCANCLK cycles

Table 1–20. Cyclone III Devices PLL Specifications (1) (Part 2 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
$f_{SCANCLK}$	scanclk frequency	—	—	100	MHz

Notes to Table 1–20:

(1) V_{CCD_PLL} should always be connected to V_{CCINT} through decoupling capacitor and ferrite bead.
(2) This parameter is limited in the Quartus II software by the I/O maximum frequency. The maximum I/O frequency is different for each I/O standard.
(3) The V_{CO} frequency reported by the Quartus II software in the PLL summary section of the compilation report takes into consideration the V_{CO} post-scale counter K value. Therefore, if the counter K has a value of 2, the frequency reported can be lower than the f_{VCO} specification.
(4) A high input jitter directly affects the PLL output jitter. To have low PLL output clock jitter, you must provide a clean clock source, which is less than 200 ps.
(5) Peak-to-peak jitter with a probability level of 10^{-12} (14 sigma, 99.99999999974404% confidence level). The output jitter specification applies to the intrinsic jitter of the PLL, when an input jitter of 30 ps is applied.
(6) With 100 MHz scanclk frequency.

Embedded Multiplier Specifications

Table 1–21 describes the embedded multiplier specifications for Cyclone III devices.

Table 1–21. Cyclone III Devices Embedded Multiplier Specifications

Mode	Resources Used	Performance			Unit
	Number of Multipliers	C6	C7, I7, A7	C8	
9 × 9-bit multiplier	1	340	300	260	MHz
18 × 18-bit multiplier	1	287	250	200	MHz

Memory Block Specifications

Table 1–22 describes the M9K memory block specifications for Cyclone III devices.

Table 1–22. Cyclone III Devices Memory Block Performance Specifications

Memory	Mode	Resources Used		Performance			
		LEs	M9K Memory	C6	C7, I7, A7	C8	Unit
M9K Block	FIFO 256 × 36	47	1	315	274	238	MHz
	Single-port 256 × 36	0	1	315	274	238	MHz
	Simple dual-port 256 × 36 CLK	0	1	315	274	238	MHz
	True dual port 512 × 18 single CLK	0	1	315	274	238	MHz

Configuration and JTAG Specifications

Table 1–23 lists the configuration mode specifications for Cyclone III devices.

Table 1–23. Cyclone III Devices Configuration Mode Specifications

Programming Mode	DCLK F_{max}	Unit
Passive Serial (PS)	133	MHz
Fast Passive Parallel (FPP) (1)	100	MHz

Note to Table 1–23:

(1) EP3C40 and smaller density members support 133 MHz.

Table 1–24 lists the active configuration mode specifications for Cyclone III devices.

Table 1–24. Cyclone III Devices Active Configuration Mode Specifications

Programming Mode	DCLK Range	Unit
Active Parallel (AP)	20 – 40	MHz
Active Serial (AS)	20 – 40	MHz

Table 1–25 lists the JTAG timing parameters and values for Cyclone III devices.

Table 1–25. Cyclone III Devices JTAG Timing Parameters *(1)*

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	40	—	ns
t_{JCH}	TCK clock high time	20	—	ns
t_{JCL}	TCK clock low time	20	—	ns
t_{JPSU_TDI}	JTAG port setup time for TDI	1	—	ns
t_{JPSU_TMS}	JTAG port setup time for TMS	3	—	ns
t_{JPH}	JTAG port hold time	10	—	ns
t_{JPCO}	JTAG port clock to output *(2)*	—	15	ns
t_{JPZX}	JTAG port high impedance to valid output *(2)*	—	15	ns
t_{JPXZ}	JTAG port valid output to high impedance *(2)*	—	15	ns
t_{JSSU}	Capture register setup time	5	—	ns
t_{JSH}	Capture register hold time	10	—	ns
t_{JSCO}	Update register clock to output	—	25	ns
t_{JSZX}	Update register high impedance to valid output	—	25	ns
t_{JSXZ}	Update register valid output to high impedance	—	25	ns

Notes to Table 1–25:

(1) For more information about JTAG waveforms, refer to "JTAG Waveform" in "Glossary" on page 1–27.

(2) The specification is shown for 3.3-, 3.0-, and 2.5-V LVTTL/LVCMOS operation of JTAG pins. For 1.8-V LVTTL/LVCMOS and 1.5-V LVCMOS, the JTAG port clock to output time is 16 ns.

Periphery Performance

This section describes periphery performance, including high-speed I/O, external memory interface, and IOE programmable delay.

I/O performance supports several system interfacing, for example, the high-speed I/O interface, external memory interface, and the PCI/PCI-X bus interface. I/O using the SSTL-18 Class I termination standard can achieve up to the stated DDR2 SDRAM interfacing speeds with typical DDR SDRAM memory interface setup. I/O using general-purpose I/O standards such as 3.0-, 2.5-, 1.8-, or 1.5-LVTTL/LVCMOS are capable of a typical 200 MHz interfacing frequency with a 10 pF load.



Actual achievable frequency depends on design- and system-specific factors. Perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specifications

Table 1–26 through Table 1–31 list the high-speed I/O timing for Cyclone III devices. For definitions of high-speed timing specifications, refer to "Glossary" on page 1–27.

Table 1–26. Cyclone III Devices RSDS Transmitter Timing Specifications *(1), (2)*

Symbol	Modes	C6			C7, I7			C8, A7			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK} (input clock frequency)	×10	5	—	180	5	—	155.5	5	—	155.5	MHz
	×8	5	—	180	5	—	155.5	5	—	155.5	MHz
	×7	5	—	180	5	—	155.5	5	—	155.5	MHz
	×4	5	—	180	5	—	155.5	5	—	155.5	MHz
	×2	5	—	180	5	—	155.5	5	—	155.5	MHz
	×1	5	—	360	5	—	311	5	—	311	MHz
Device operation in Mbps	×10	100	—	360	100	—	311	100	—	311	Mbps
	×8	80	—	360	80	—	311	80	—	311	Mbps
	×7	70	—	360	70	—	311	70	—	311	Mbps
	×4	40	—	360	40	—	311	40	—	311	Mbps
	×2	20	—	360	20	—	311	20	—	311	Mbps
	×1	10	—	360	10	—	311	10	—	311	Mbps
t_{DUTY}	—	45	—	55	45	—	55	45	—	55	%
TCCS	—	—	—	200	—	—	200	—	—	200	ps
Output jitter (peak to peak)	—	—	—	500	—	—	500	—	—	550	ps
t_{RISE}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{FALL}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{LOCK} *(3)*	—	—	—	1	—	—	1	—	—	1	ms

Notes to Table 1–26:

(1) Applicable for true RSDS and emulated RSDS_E_3R transmitter.

(2) True RSDS transmitter is only supported at output pin of Row I/O (Banks 1, 2, 5, and 6). Emulated RSDS transmitter is supported at the output pin of all I/O banks.

(3) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

Table 1–27. Cyclone III Devices Emulated RSDS_E_1R Transmitter Timing Specifications *(1)* **(Part 1 of 2)**

Symbol	Modes	C6			C7, I7			C8, A7			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK} (input clock frequency)	×10	5	—	85	5	—	85	5	—	85	MHz
	×8	5	—	85	5	—	85	5	—	85	MHz
	×7	5	—	85	5	—	85	5	—	85	MHz
	×4	5	—	85	5	—	85	5	—	85	MHz
	×2	5	—	85	5	—	85	5	—	85	MHz
	×1	5	—	170	5	—	170	5	—	170	MHz

Table 1–27. Cyclone III Devices Emulated RSDS_E_1R Transmitter Timing Specifications (1) (Part 2 of 2)

Symbol	Modes	C6			C7, I7			C8, A7			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Device operation in Mbps	×10	100	—	170	100	—	170	100	—	170	Mbps
	×8	80	—	170	80	—	170	80	—	170	Mbps
	×7	70	—	170	70	—	170	70	—	170	Mbps
	×4	40	—	170	40	—	170	40	—	170	Mbps
	×2	20	—	170	20	—	170	20	—	170	Mbps
	×1	10	—	170	10	—	170	10	—	170	Mbps
t_{DUTY}	—	45	—	55	45	—	55	45	—	55	%
TCCS	—	—	—	200	—	—	200	—	—	200	ps
Output jitter (peak to peak)	—	—	—	500	—	—	500	—	—	550	ps
t_{RISE}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{FALL}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{LOCK} (2)	—	—	—	1	—	—	1	—	—	1	ms

Notes to Table 1–27:

(1) Emulated RSDS_E_1R transmitter is supported at the output pin of all I/O banks.

(2) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

Table 1–28. Cyclone III Devices Mini-LVDS Transmitter Timing Specifications (1), (2) (Part 1 of 2)

Symbol	Modes	C6			C7, I7			C8, A7			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK} (input clock frequency)	×10	5	—	200	5	—	155.5	5	—	155.5	MHz
	×8	5	—	200	5	—	155.5	5	—	155.5	MHz
	×7	5	—	200	5	—	155.5	5	—	155.5	MHz
	×4	5	—	200	5	—	155.5	5	—	155.5	MHz
	×2	5	—	200	5	—	155.5	5	—	155.5	MHz
	×1	5	—	400	5	—	311	5	—	311	MHz
Device operation in Mbps	×10	100	—	400	100	—	311	100	—	311	Mbps
	×8	80	—	400	80	—	311	80	—	311	Mbps
	×7	70	—	400	70	—	311	70	—	311	Mbps
	×4	40	—	400	40	—	311	40	—	311	Mbps
	×2	20	—	400	20	—	311	20	—	311	Mbps
	×1	10	—	400	10	—	311	10	—	311	Mbps
t_{DUTY}	—	45	—	55	45	—	55	45	—	55	%
TCCS	—	—	—	200	—	—	200	—	—	200	ps

Table 1–28. Cyclone III Devices Mini-LVDS Transmitter Timing Specifications (1), (2) (Part 2 of 2)

Symbol	Modes	C6			C7, I7			C8, A7			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Output jitter (peak to peak)	—	—	—	500	—	—	500	—	—	550	ps
t_{RISE}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{FALL}	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{LOCK} (3)	—	—	—	1	—	—	1	—	—	1	ms

Notes to Table 1–28:

(1) Applicable for true and emulated mini-LVDS transmitter.

(2) True mini-LVDS transmitter is only supported at the output pin of Row I/O (Banks 1, 2, 5, and 6). Emulated mini-LVDS transmitter is supported at the output pin of all I/O banks.

(3) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

Table 1–29. Cyclone III Devices True LVDS Transmitter Timing Specifications *(1)*

Symbol	Modes	C6		C7, I7		C8, A7		Unit
		Min	Max	Min	Max	Min	Max	
f_{HSCLK} (input clock frequency)	×10	5	420	5	370	5	320	MHz
	×8	5	420	5	370	5	320	MHz
	×7	5	420	5	370	5	320	MHz
	×4	5	420	5	370	5	320	MHz
	×2	5	420	5	370	5	320	MHz
	×1	5	420	5	402.5	5	402.5	MHz
HSIODR	×10	100	840	100	740	100	640	Mbps
	×8	80	840	80	740	80	640	Mbps
	×7	70	840	70	740	70	640	Mbps
	×4	40	840	40	740	40	640	Mbps
	×2	20	840	20	740	20	640	Mbps
	×1	10	420	10	402.5	10	402.5	Mbps
t_{DUTY}	—	45	55	45	55	45	55	%
TCCS	—	—	200	—	200	—	200	ps
Output jitter (peak to peak)	—	—	500	—	500	—	550	ps
t_{LOCK} *(2)*	—	—	1	—	1	—	1	ms

Notes to Table 1–29:

(1) True LVDS transmitter is only supported at the output pin of Row I/O (Banks 1, 2, 5, and 6).

(2) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

Table 1–30. Cyclone III Devices Emulated LVDS Transmitter Timing Specifications *(1)* **(Part 1 of 2)**

Symbol	Modes	C6		C7, I7		C8, A7		Unit
		Min	Max	Min	Max	Min	Max	
f_{HSCLK} (input clock frequency)	×10	5	320	5	320	5	275	MHz
	×8	5	320	5	320	5	275	MHz
	×7	5	320	5	320	5	275	MHz
	×4	5	320	5	320	5	275	MHz
	×2	5	320	5	320	5	275	MHz
	×1	5	402.5	5	402.5	5	402.5	MHz
HSIODR	×10	100	640	100	640	100	550	Mbps
	×8	80	640	80	640	80	550	Mbps
	×7	70	640	70	640	70	550	Mbps
	×4	40	640	40	640	40	550	Mbps
	×2	20	640	20	640	20	550	Mbps
	×1	10	402.5	10	402.5	10	402.5	Mbps
t_{DUTY}	—	45	55	45	55	45	55	%
TCCS	—	—	200	—	200	—	200	ps

Table 1–30. Cyclone III Devices Emulated LVDS Transmitter Timing Specifications (1) (Part 2 of 2)

Symbol	Modes	C6		C7, I7		C8, A7		Unit
		Min	Max	Min	Max	Min	Max	
Output jitter (peak to peak)	—	—	500	—	500	—	550	ps
t_{LOCK} (2)	—	—	1	—	1	—	1	ms

Notes to Table 1–30:

(1) Emulated LVDS transmitter is supported at the output pin of all I/O banks.

(2) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

Table 1–31. Cyclone III Devices LVDS Receiver Timing Specifications (1)

Symbol	Modes	C6		C7, I7		C8, A7		Unit
		Min	Max	Min	Max	Min	Max	
f_{HSCLK} (input clock frequency)	×10	5	437.5	5	370	5	320	MHz
	×8	5	437.5	5	370	5	320	MHz
	×7	5	437.5	5	370	5	320	MHz
	×4	5	437.5	5	370	5	320	MHz
	×2	5	437.5	5	370	5	320	MHz
	×1	5	437.5	5	402.5	5	402.5	MHz
HSIODR	×10	100	875	100	740	100	640	Mbps
	×8	80	875	80	740	80	640	Mbps
	×7	70	875	70	740	70	640	Mbps
	×4	40	875	40	740	40	640	Mbps
	×2	20	875	20	740	20	640	Mbps
	×1	10	437.5	10	402.5	10	402.5	Mbps
SW	—	—	400	—	400	—	400	ps
Input jitter tolerance	—	—	500	—	500	—	550	ps
t_{LOCK} (2)	—	—	1	—	1	—	1	ms

Notes to Table 1–31:

(1) LVDS receiver is supported at all banks.

(2) t_{LOCK} is the time required for the PLL to lock from the end of device configuration.

External Memory Interface Specifications

Cyclone III devices support external memory interfaces up to 200 MHz. The external memory interfaces for Cyclone III devices are auto-calibrating and easy to implement.

For more information about external memory system performance specifications, board design guidelines, timing analysis, simulation, and debugging information, refer to *Literature: External Memory Interfaces*.

Table 1–32 lists the FPGA sampling window specifications for Cyclone III devices.

Table 1–32. Cyclone III Devices FPGA Sampling Window (SW) Requirement – Read Side (1)

Memory Standard	Column I/Os		Row I/Os		Wraparound Mode	
	Setup	Hold	Setup	Hold	Setup	Hold
C6						
DDR2 SDRAM	580	550	690	640	850	800
DDR SDRAM	585	535	700	650	870	820
QDRII SRAM	785	735	805	755	905	855
C7						
DDR2 SDRAM	705	650	770	715	985	930
DDR SDRAM	675	620	795	740	970	915
QDRII SRAM	900	845	910	855	1085	1030
C8						
DDR2 SDRAM	785	720	930	870	1115	1055
DDR SDRAM	800	740	915	855	1185	1125
QDRII SRAM	1050	990	1065	1005	1210	1150
I7						
DDR2 SDRAM	765	710	855	800	1040	985
DDR SDRAM	745	690	880	825	1000	945
QDRII SRAM	945	890	955	900	1130	1075
A7						
DDR2 SDRAM	805	745	1020	960	1145	1085
DDR SDRAM	880	820	955	935	1220	1160
QDRII SRAM	1090	1030	1105	1045	1250	1190

Note to Table 1–32:

(1) Column I/Os refer to top and bottom I/Os. Row I/Os refer to right and left I/Os. Wraparound mode refers to the combination of column and row I/Os.

Table 1–33 lists the transmitter channel-to-channel skew specifications for Cyclone III devices.

Table 1–33. Cyclone III Devices Transmitter Channel-to-Channel Skew (TCCS) – Write Side (1) (Part 1 of 2)

Memory Standard	I/O Standard	Column I/Os (ps)		Row I/Os (ps)		Wraparound Mode (ps)	
		Lead	Lag	Lead	Lag	Lead	Lag
C6							
DDR2 SDRAM	SSTL-18 Class I	790	380	790	380	890	480
	SSTL-18 Class II	870	490	870	490	970	590
DDR SDRAM	SSTL-2 Class I	750	320	750	320	850	420
	SSTL-2 Class II	860	350	860	350	960	450
QDRII SRAM	1.8 V HSTL Class I	780	410	780	410	880	510
	1.8 V HSTL Class II	830	510	830	510	930	610
C7							

Table 1–33. Cyclone III Devices Transmitter Channel-to-Channel Skew (TCCS) – Write Side (1) (Part 2 of 2)

Memory Standard	I/O Standard	Column I/Os (ps)		Row I/Os (ps)		Wraparound Mode (ps)	
		Lead	Lag	Lead	Lag	Lead	Lag
DDR2 SDRAM	SSTL-18 Class I	915	410	915	410	1015	510
	SSTL-18 Class II	1025	545	1025	545	1125	645
DDR SDRAM	SSTL-2 Class I	880	340	880	340	980	440
	SSTL-2 Class II	1010	380	1010	380	1110	480
QDRII SRAM	1.8 V HSTL Class I	910	450	910	450	1010	550
	1.8 V HSTL Class II	1010	570	1010	570	1110	670
C8							
DDR2 SDRAM	SSTL-18 Class I	1040	440	1040	440	1140	540
	SSTL-18 Class II	1180	600	1180	600	1280	700
DDR SDRAM	SSTL-2 Class I	1010	360	1010	360	1110	460
	SSTL-2 Class II	1160	410	1160	410	1260	510
QDRII SRAM	1.8 V HSTL Class I	1040	490	1040	490	1140	590
	1.8 V HSTL Class II	1190	630	1190	630	1290	730
I7							
DDR2 SDRAM	SSTL-18 Class I	961	431	961	431	1061	531
	SSTL-18 Class II	1076	572	1076	572	1176	672
DDR SDRAM	SSTL-2 Class I	924	357	924	357	1024	457
	SSTL-2 Class II	1061	399	1061	399	1161	499
QDRII SRAM	1.8 V HSTL Class I	956	473	956	473	1056	573
	1.8 V HSTL Class II	1061	599	1061	599	1161	699
A7							
DDR2 SDRAM (2)	SSTL-18 Class I	1092	462	1092	462	1192	562
	SSTL-18 Class II	1239	630	1239	630	1339	730
DDR SDRAM	SSTL-2 Class I	1061	378	1061	378	1161	478
	SSTL-2 Class II	1218	431	1218	431	1318	531
QDRII SRAM	1.8 V HSTL Class I	1092	515	1092	515	1192	615
	1.8 V HSTL Class II	1250	662	1250	662	1350	762

Notes to Table 1–33:

(1) Column I/O banks refer to top and bottom I/Os. Row I/O banks refer to right and left I/Os. Wraparound mode refers to the combination of column and row I/Os.

(2) For DDR2 SDRAM write timing performance on Columns I/O for C8 and A7 devices, 97.5 degree phase offset is required.

Table 1–34 lists the memory output clock jitter specifications for Cyclone III devices.

Table 1–34. Cyclone III Devices Memory Output Clock Jitter Specifications (1), (2) (Part 1 of 2)

Parameter	Symbol	Min	Max	Unit
Clock period jitter	$t_{JIT(per)}$	-125	125	ps
Cycle-to-cycle period jitter	$t_{JIT(cc)}$	-200	200	ps

Table 1–34. Cyclone III Devices Memory Output Clock Jitter Specifications (1), (2) (Part 2 of 2)

Parameter	Symbol	Min	Max	Unit
Duty cycle jitter	$t_{JIT(duty)}$	-150	150	ps

Notes to Table 1–34:

(1) The memory output clock jitter measurements are for 200 consecutive clock cycles, as specified in the JEDEC DDR2 standard.

(2) The clock jitter specification applies to memory output clock pins generated using DDIO circuits clocked by a PLL output routed on a global clock network.

Duty Cycle Distortion Specifications

Table 1–35 lists the worst case duty cycle distortion for Cyclone III devices.

Table 1–35. Duty Cycle Distortion on Cyclone III Devices I/O Pins (1), (2)

Symbol	C6		C7, I7		C8, A7		Unit
	Min	Max	Min	Max	Min	Max	
Output Duty Cycle	45	55	45	55	45	55	%

Notes to Table 1–35:

(1) Duty cycle distortion specification applies to clock outputs from PLLs, global clock tree, and IOE driving dedicated and general purpose I/O pins.

(2) Cyclone III devices meet specified duty cycle distortion at maximum output toggle rate for each combination of I/O standard and current strength.

OCT Calibration Timing Specification

Table 1–36 lists the duration of calibration for series OCT with calibration at device power-up for Cyclone III devices.

Table 1–36. Cyclone III Devices Timing Specification for Series OCT with Calibration at Device Power-Up (1)

Symbol	Description	Maximum	Unit
t_{OCTCAL}	Duration of series OCT with calibration at device power-up	20	µs

Notes to Table 1–36:

(1) OCT calibration takes place after device configuration, before entering user mode.

IOE Programmable Delay

Table 1–37 and Table 1–38 list IOE programmable delay for Cyclone III devices.

Table 1–37. Cyclone III Devices IOE Programmable Delay on Column Pins (1), (2) (Part 1 of 2)

Parameter	Paths Affected	Number of Settings	Min Offset	Max Offset							Unit
				Fast Corner		Slow Corner					
				A7, I7	C6	C6	C7	C8	I7	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.211	1.314	2.175	2.32	2.386	2.366	2.49	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.203	1.307	2.19	2.387	2.54	2.43	2.545	ns

Table 1–37. Cyclone III Devices IOE Programmable Delay on Column Pins (1), (2) (Part 2 of 2)

Parameter	Paths Affected	Number of Settings	Min Offset	Max Offset							Unit
				Fast Corner		Slow Corner					
				A7, I7	C6	C6	C7	C8	I7	A7	
Delay from output register to output pin	I/O output register to pad	2	0	0.479	0.504	0.915	1.011	1.107	1.018	1.048	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.664	0.694	1.199	1.378	1.532	1.392	1.441	ns

Notes to Table 1–37:

(1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting '0' as available in the Quartus II software.

Table 1–38. Cyclone III Devices IOE Programmable Delay on Row Pins (1), (2)

Parameter	Paths Affected	Number of Settings	Min Offset	Max Offset							Unit
				Fast Corner		Slow Corner					
				A7, I7	C6	C6	C7	C8	I7	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.209	1.314	2.174	2.335	2.406	2.381	2.505	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.207	1.312	2.202	2.402	2.558	2.447	2.557	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.51	0.537	0.962	1.072	1.167	1.074	1.101	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.669	0.698	1.207	1.388	1.542	1.403	1.45	ns

Notes to Table 1–38:

(1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting '0' as available in the Quartus II software

I/O Timing

You can use the following methods to determine the I/O timing:

- the Excel-based I/O Timing.
- the Quartus II timing analyzer.

The Excel-based I/O Timing provides pin timing performance for each device density and speed grade. The data is typically used prior to designing the FPGA to get a timing budget estimation as part of the link timing analysis. The Quartus II timing analyzer provides a more accurate and precise I/O timing data based on the specifics of the design after place-and-route is complete.

The Excel-based I/O Timing spreadsheet is downloadable from Cyclone III Devices Literature website.

Glossary

Table 1–39 lists the glossary for this chapter.

Table 1–39. Glossary (Part 1 of 5)

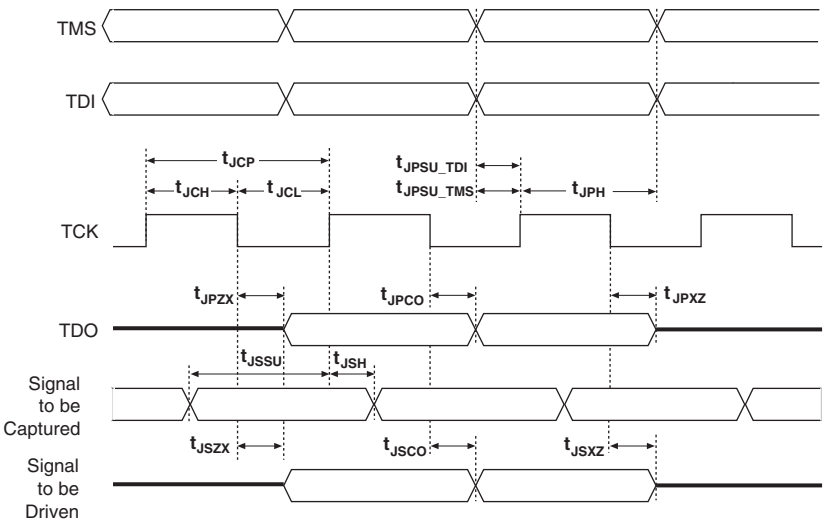
Letter	Term	Definitions
A	—	—
B	—	—
C	—	—
D	—	—
E	—	—
F	f_{HSCLK}	HIGH-SPEED I/O Block: High-speed receiver/transmitter input and output clock frequency.
G	GCLK	Input pin directly to Global Clock network.
	GCLK PLL	Input pin to Global Clock network through PLL.
H	HSIODR	HIGH-SPEED I/O Block: Maximum/minimum LVDS data transfer rate (HSIODR = 1/TUI).
I	Input Waveforms for the SSTL Differential I/O Standard	
J	JTAG Waveform	
K	—	—
L	—	—
M	—	—

Table 1–39. Glossary (Part 2 of 5)

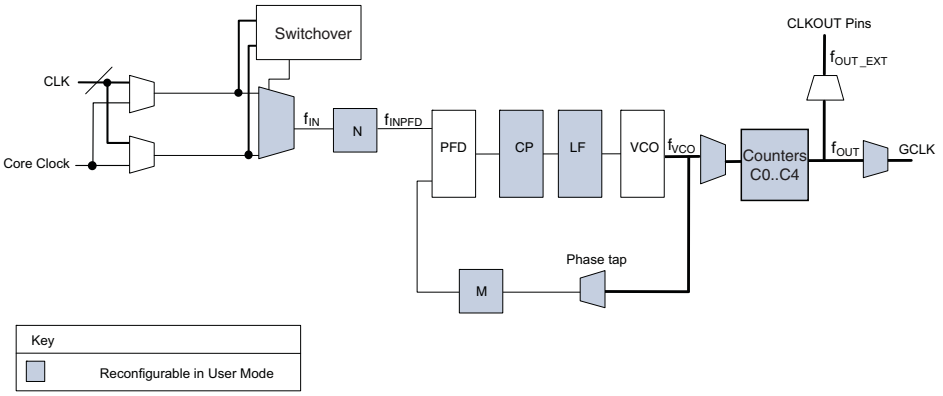
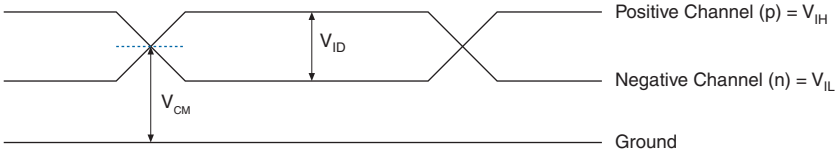
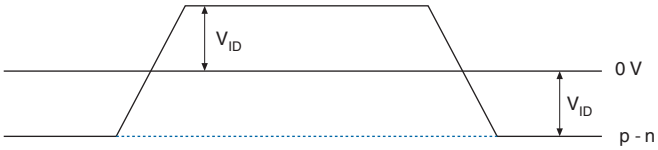
Letter	Term	Definitions
N	—	—
O	—	—
P	PLL Block	The following block diagram highlights the PLL Specification parameters. 
Q	—	—
R	R_L	Receiver differential input discrete resistor (external to Cyclone III devices).
	Receiver Input Waveform	Receiver Input Waveform for LVDS and LVPECL Differential Standards. **Single-Ended Waveform**  **Differential Waveform (Mathematical Function of Positive & Negative Channel)** 
	RSKM (Receiver input skew margin)	HIGH-SPEED I/O Block: The total margin left after accounting for the sampling window and TCCS. RSKM = (TUI – SW – TCCS) / 2.

Table 1–39. Glossary (Part 3 of 5)

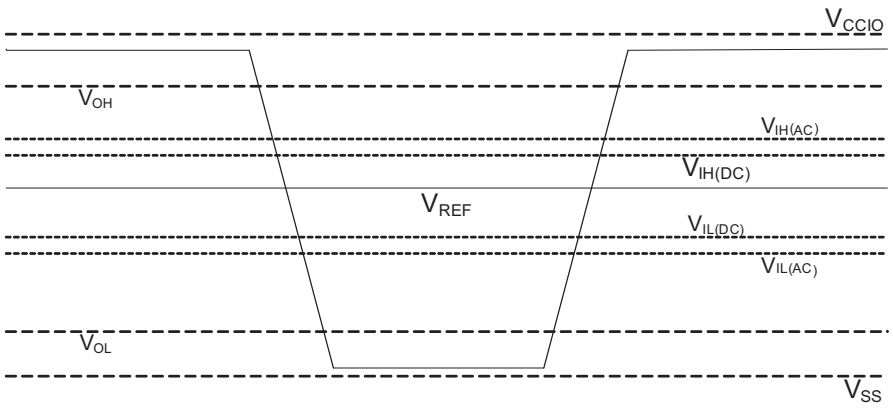
Letter	Term	Definitions
S	Single-ended Voltage referenced I/O Standard	 The JEDEC standard for SSTI and HSTL I/O standards defines both the AC and DC input signal values. The AC values indicate the voltage levels at which the receiver must meet its timing specifications. The DC values indicate the voltage levels at which the final logic state of the receiver is unambiguously defined. After the receiver input crosses the AC value, the receiver changes to the new logic state. The new logic state is then maintained as long as the input stays beyond the DC threshold. This approach is intended to provide predictable receiver timing in the presence of input waveform *ringing*.
	SW (Sampling Window)	HIGH-SPEED I/O Block: The period of time during which the data must be valid to capture it correctly. The setup and hold times determine the ideal strobe position in the sampling window.
T	t_C	High-speed receiver/transmitter input and output clock period.
	TCCS (Channel-to-channel-skew)	HIGH-SPEED I/O Block: The timing difference between the fastest and slowest output edges, including t_{CO} variation and clock skew. The clock is included in the TCCS measurement.
	tcin	Delay from clock pad to I/O input register.
	t_{CO}	Delay from clock pad to I/O output.
	tcout	Delay from clock pad to I/O output register.
	t_{DUTY}	HIGH-SPEED I/O Block: Duty cycle on high-speed transmitter output clock.
	t_{FALL}	Signal High-to-low transition time (80–20%).
	t_H	Input register hold time.
	Timing Unit Interval (TUI)	HIGH-SPEED I/O block: The timing budget allowed for skew, propagation delays, and data sampling window. (TUI = 1/(Receiver Input Clock Frequency Multiplication Factor) = t_C/w).
	$t_{INJITTER}$	Period jitter on PLL clock input.
	$t_{OUTJITTER_DEDCLK}$	Period jitter on dedicated clock output driven by a PLL.
	$t_{OUTJITTER_IO}$	Period jitter on general purpose I/O driven by a PLL.
	tpllcin	Delay from PLL inclk pad to I/O input register.
	tpllcout	Delay from PLL inclk pad to I/O output register.

Table 1–39. Glossary (Part 4 of 5)

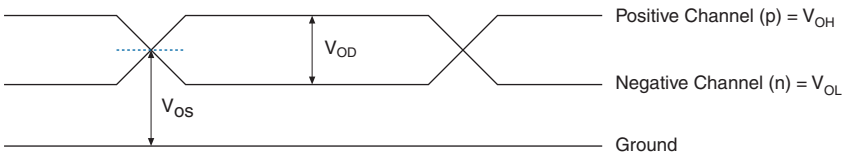
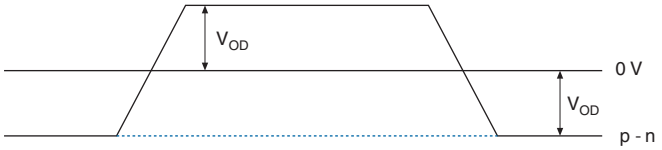
Letter	Term	Definitions
	Transmitter Output Waveform	Transmitter Output Waveforms for the LVDS, mini-LVDS, PPDS and RSDS Differential I/O Standards **Single-Ended Waveform**  **Differential Waveform (Mathematical Function of Positive & Negative Channel)** 
	t_{RISE}	Signal Low-to-high transition time (20–80%).
	t_{SU}	Input register setup time.
U	—	—

Table 1–39. Glossary (Part 5 of 5)

Letter	Term	Definitions
V	$V_{CM(DC)}$	DC Common Mode Input Voltage.
	$V_{DIF(AC)}$	AC differential Input Voltage: The minimum AC input differential voltage required for switching.
	$V_{DIF(DC)}$	DC differential Input Voltage: The minimum DC input differential voltage required for switching.
	V_{ICM}	Input Common Mode Voltage: The common mode of the differential signal at the receiver.
	V_{ID}	Input differential Voltage Swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the receiver.
	V_{IH}	Voltage Input High: The minimum positive voltage applied to the input which is accepted by the device as a logic high.
	$V_{IH(AC)}$	High-level AC input voltage.
	$V_{IH(DC)}$	High-level DC input voltage.
	V_{IL}	Voltage Input Low: The maximum positive voltage applied to the input which is accepted by the device as a logic low.
	$V_{IL\ (AC)}$	Low-level AC input voltage.
	$V_{IL\ (DC)}$	Low-level DC input voltage.
	V_{IN}	DC input voltage.
	V_{OCM}	Output Common Mode Voltage: The common mode of the differential signal at the transmitter.
	V_{OD}	Output differential Voltage Swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the transmitter. $V_{OD} = V_{OH} – V_{OL}$.
	V_{OH}	Voltage Output High: The maximum positive voltage from an output which the device considers is accepted as the minimum positive high level.
	V_{OL}	Voltage Output Low: The maximum positive voltage from an output which the device considers is accepted as the maximum positive low level.
	V_{OS}	Output offset voltage: $V_{OS} = (V_{OH} + V_{OL}) / 2$.
	$V_{OX\ (AC)}$	AC differential Output cross point voltage: The voltage at which the differential output signals must cross.
	V_{REF}	Reference voltage for SSTL, HSTL I/O Standards.
	$V_{REF\ (AC)}$	AC input reference voltage for SSTL, HSTL I/O Standards. $V_{REF(AC)} = V_{REF(DC)}$ + noise. The peak-to-peak AC noise on V_{REF} should not exceed 2% of $V_{REF(DC)}$.
	$V_{REF\ (DC)}$	DC input reference voltage for SSTL, HSTL I/O Standards.
	$V_{SWING\ (AC)}$	AC differential Input Voltage: AC Input differential voltage required for switching. For the SSTL Differential I/O Standard, refer to Input Waveforms.
	$V_{SWING\ (DC)}$	DC differential Input Voltage: DC Input differential voltage required for switching. For the SSTL Differential I/O Standard, refer to Input Waveforms.
	V_{TT}	Termination voltage for SSTL, HSTL I/O Standards.
	$V_{X\ (AC)}$	AC differential Input cross point Voltage: The voltage at which the differential input signals must cross.
W	—	—
X	—	—
Y	—	—
Z	—	—

Document Revision History

Table 1–40 lists the revision history for this document.

Table 1–40. Document Revision History (Part 1 of 3)

Date	Version	Changes
July 2012	3.5	Updated minimum f_{HSCLK} value to 5 MHz.
December 2011	3.4	■ Updated "Supply Current" on page 1–5 and "Periphery Performance" on page 1–17. ■ Updated Table 1–3, Table 1–4, Table 1–13, Table 1–16, Table 1–17, Table 1–20, and Table 1–25.
January 2010	3.3	■ Removed Table 1-32 and Table 1-33. ■ Added *Literature: External Memory Interfaces reference*.
December 2009	3.2	Minor changes to the text.
July 2009	3.1	Minor edit to the hyperlinks.
June 2009	3.0	■ Changed chapter title from DC and Switching Characteristics to "Cyclone III Device Data Sheet" on page 1–1. ■ Updated *(Note 1)* to Table 1–23 on page 1–17. ■ Updated "External Memory Interface Specifications" on page 1–23. ■ Replaced Table 1–32 on page 1–23. ■ Replaced Table 1–33 on page 1–23. ■ Added Table 1–36 on page 1–26. ■ Updated "I/O Timing" on page 1–28. ■ Removed "Typical Design Performance" section. ■ Removed "I/O Timing" subsections.
October 2008	2.2	■ Updated chapter to new template. ■ Updated Table 1–1, Table 1–3, and Table 1–18. ■ Added *(Note 7)* to Table 1–3. ■ Added the "OCT Calibration Timing Specification" section. ■ Updated "Glossary" section.
July 2008	2.1	■ Updated Table 1–38. ■ Added BLVDS information (I/O standard) into Table 1–39, Table 1–40, Table 1–41, Table 1–42. ■ Updated Table 1–43, Table 1–46, Table 1–47, Table 1–48, Table 1–49, Table 1–50, Table 1–51, Table 1–52, Table 1–53, Table 1–54, Table 1–55, Table 1–56, Table 1–57, Table 1–58, Table 1–59, Table 1–60, Table 1–61, Table 1–62, Table 1–63, Table 1–68, Table 1–69, Table 1–74, Table 1–75, Table 1–80, Table 1–81, Table 1–86, Table 1–87, Table 1–92, Table 1–93, Table 1–94, Table 1–95, Table 1–96, Table 1–97, Table 1–98, and Table 1–99.

Table 1–40. Document Revision History (Part 2 of 3)

Date	Version	Changes
May 2008	2.0	■ Updated "Operating Conditions" section and included information on automotive device. ■ Updated Table 1–3, Table 1–6, and Table 1–7, and added automotive information. ■ Under "Pin Capacitance" section, updated Table 1–9 and Table 1–10. ■ Added new "Schmitt Trigger Input" section with Table 1–12. ■ Under "I/O Standard Specifications" section, updated Table 1–13, 1–12 and 1–12. ■ Under "Switching Characteristics" section, updated Table 1–19, 1–15, 1–16, 1–16, 1–17, 1–18, 1–19, 1–20, 1–21, 1–21, 1–23, 1–23, 1–23, 1–24, and 1–25. ■ Updated Figure 1–5 and 1–29. ■ Deleted previous Table 1-35 "DDIO Outputs Half-Period Jitter". ■ Under "I/O Timing" section, updated Table 1–38, 1–29, 1–32, 1–33, 1–26, and 1–26. ■ Under "Typical Design Performance" section updated Table 1–46 through 1–145.
December 2007	1.5	■ Under "Core Performance Specifications", updated Tables 1-18 and 1-19. ■ Under "Preliminary, Correlated, and Final Timing", updated Table 1-37. ■ Under "Typical Design Performance", updated Tables 1-45, 1-46, 1-51, 1-52, 1-57, 1-58, Tables 1-63 through 1-68. 1-69, 1-70, 1-75, 1-76, 1-81, 1-82, Tables 1-87 through 1-92, Tables 1-99, 1-100, 1-107, and 1-108.
October 2007	1.4	■ Updated the C_{VREFTB} value in Table 1-9. ■ Updated Table 1-21. ■ Under "High-Speed I/O Specification" section, updated Tables 1-25 through 1-30. ■ Updated Tables 1-31 through 1-38. ■ Added new Table 1-32. ■ Under "Maximum Input and Output Clock Toggle Rate" section, updated Tables 1-40 through 1-42. ■ Under "IOE Programmable Delay" section, updated Tables 1-43 through 1-44. ■ Under "User I/O Pin Timing Parameters" section, updated Tables 1-45 through 1-92. ■ Under "Dedicated Clock Pin Timing Parameters" section, updated Tables 1-93 through 1-108.
July 2007	1.3	■ Updated Table 1-1 with V_{ESDHBM} and V_{ESDCDM} information. ■ Updated R_{CONF_PD} information in Tables 1-10. ■ Added *Note (3)* to Table 1-12. ■ Updated t_{DLOCK} information in Table 1-19. ■ Updated Table 1-43 and Table 1-44. ■ Added "Document Revision History" section.
June 2007	1.2	Updated Cyclone III graphic in cover page.

Table 1–40. Document Revision History (Part 3 of 3)

Date	Version	Changes
May 2007	1.1	■ Corrected current unit in Tables 1-1, 1-12, and 1-14. ■ Added *Note (3)* to Table 1-3. ■ Updated Table 1-4 with I_{CCINT0}, I_{CCA0}, I_{CCD_PLL0}, and I_{CCIO0} information. ■ Updated Table 1-9 and added *Note (2)*. ■ Updated Table 1-19. ■ Updated Table 1-22 and added *Note (1)*. ■ Changed I/O standard from 1.5-V LVTTL/LVCMOS and 1.2-V LVTTL/LVCMOS to 1.5-V LVCMOS and 1.2-V LVCMOS in Tables 1-41, 1-42, 1-43, 1-44, and 1-45. ■ Updated Table 1-43 with changes to LVPEC and LVDS and added *Note (5)*. ■ Updated Tables 1-46, 1-47, Tables 1-54 through 1-95, and Tables 1-98 through 1-111. ■ Removed speed grade –6 from Tables 1-90 through 1-95, and from Tables 1-110 through 1-111. ■ Added a waveform (Receiver Input Waveform) in glossary under letter “R” (Table 1-112).
March 2007	1.0	Initial release.